

Amendments to the Specification

Please replace the paragraph beginning on page 3, line 15 to page 4 line 9, with the following rewritten paragraph:

Here, the conductive metal film also includes a conductive metal oxide film. A conductive metal film can be formed by supplying the gas obtained by vaporizing the organic source ~~organic source~~ to a substrate and then supplying gas excited by plasma to react with the gas obtained by vaporizing the organic source. In the metal film, elements in an organic source captured as impurities into the film can be reduced by an action of plasma-excited-gas and the electric characteristic does not deteriorate even when the process temperature is reduced. Thus, improvement for film quality after the film formation is not required. Furthermore, film peeling due to impurities may not occur easily even when annealed after the film formation. Furthermore, since a film is formed by supplying source gas and then supplying plasma-excited-gas to cause a complete surface reaction, no incubation time occurs. Thus, good productivity can be achieved. Furthermore, a metal film having good step coverage can be formed. Therefore, a conductive metal film having good characteristics and high productivity can be formed.